

Shaowen Han

List of Publications by Year in descending order

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15
papers

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times ranked

467
citing authors

#	ARTICLE	IF	CITATIONS
1	Conductivity Modulation in Vertical GaN PIN Diode: Evidence and Impact. IEEE Electron Device Letters, 2021, 42, 300-303.	2.2	19
2	Vertical GaN power rectifiers: interface effects and switching performance. Semiconductor Science and Technology, 2021, 36, 024005.	1.0	5
3	Negative Dynamic RON in Vertical GaN PIN Diode: The Impact of Conductivity Modulation. , 2020, , .		1
4	Investigation of Temperature-Dependent Dynamic R_{ON} of GaN HEMT with Hybrid-Drain under Hard and Soft Switching. , 2020, , .		14
5	Surge Current Capability of GaN E-HEMTs in Reverse Conduction Mode. , 2019, , .		5
6	Investigation of Surge Current Capability of GaN E-HEMTs in The Third Quadrant: The Impact of P-GaN Contact. IEEE Journal of Emerging and Selected Topics in Power Electronics, 2019, 7, 1465-1474.	3.7	13
7	Fluorine-Implanted Termination for Vertical GaN Schottky Rectifier With High Blocking Voltage and Low Forward Voltage Drop. IEEE Electron Device Letters, 2019, 40, 1040-1043.	2.2	61
8	Dynamic On-Resistance in GaN Power Devices: Mechanisms, Characterizations, and Modeling. IEEE Journal of Emerging and Selected Topics in Power Electronics, 2019, 7, 1425-1439.	3.7	85
9	Photon-Enhanced Conductivity Modulation and Surge Current Capability in Vertical GaN Power Rectifiers. , 2019, , .		17
10	Current-Collapse-Free and Fast Reverse Recovery Performance in Vertical GaN-on-GaN Schottky Barrier Diode. IEEE Transactions on Power Electronics, 2019, 34, 5012-5018.	5.4	56
11	High-Voltage and High- I_{ON}/I_{OFF} Vertical GaN-on-GaN Schottky Barrier Diode With Nitridation-Based Termination. IEEE Electron Device Letters, 2018, 39, 572-575.	2.2	105
12	Design of Fluorine-Ion-Based Junction Termination Extension for Vertical GaN Schottky Rectifier. , 2018, , .		0
13	1 kV/1.3 m ² vertical GaN-on-GaN Schottky barrier diodes with high switching performance. , 2018, , .		4
14	Buffer trapping-induced R_{ON} degradation in GaN-on-Si power transistors: Role of electron injection from Si substrate. , 2017, , .		2
15	Impact of Substrate Bias Polarity on Buffer-Related Current Collapse in AlGaIn/GaN-on-Si Power Devices. IEEE Transactions on Electron Devices, 2017, 64, 5048-5056.	1.6	69